

DIODES

100% Probe Tested to These Parameters @ 25°C

Guaranteed tested on (sample basis)

COMPLEMENTARY SWITCHING DIODES (\*AVAILABLE IN 16 PIN DIP ARRAYS)

Part Number	$V_{BR}$ Volts Min. @ $I_R = 100 \mu A$	$I_R$ $\mu A$ Max. @ $V_R$ Volts	$I_F$ mA Min. @ $V_F = 1.0V$	$C_T$ pf Max. @ 0V	$t_{rr}$ Max. in N-Sec @ $I_F = 10mA$ ; recover to $I_R = -1 mA$	GEOM-ETRY
1N914* EQUIVALENT TO IN4148	100	5.0 @ 75V	10	4.0	4.0	Q
1N914-N	100	1.0 @ 75V	10	4.0	100	Q
1N914-R*	60	5.0 @ 50V	10	6.0	50	R
1N914-RN	60	1.0 @ 50V	10	6.0	500	R
1N914-HV	200	1.0 @ 75V	10	4.0	100	Q
1N914-B	75	5.0 @ 60V	50	4.0	4.0	Q
DE100 DF100	75	0.10	200	2	6.0	S T

HIGH POWER SWITCHING DIODES

Part Number	$V_{BR}$ Volts Min. @ $I_R = 100 \mu A$	$I_R$ $\mu A$ Max. @ $V_R$ Volts	$I_F$ mA Min. @ $V_F = 1.0V$	$C_T$ pf Max. @ 0V	$t_{rr}$ Max. in N-Sec. @ $I_F = 10mA$ ; recover to $I_R = -1 mA$	GEOM-ETRY
DE 3101/5	100	10 $\mu A$ at 90V	1.65 at 15 Amps	300 pf	35 ns	U
DE 3101/2	100	10 $\mu A$ at 90V	1.60 at 7 Amps	200 pf	35 ns	V

DIODE QUADS

Part Number	$\Delta V_F$ mV Max. @ $I_F = 1.0mA$	Matched Characteristic $V_{BR}$ Volts Min. @ $I_R = 100 \mu A$	$I_R$ $\mu A$ Max. @ $V_R$ Volts	$I_F$ mA Min. @ $V_F = 1.0V$	$C_T$ pf Max.	$t_{rr}$ Max @ $I_F = 10mA$ ; recover to $I_R = -1 mA$	GEOM-ETRY
DI 914-1Q -2Q -3Q	10	75 60 45	.025 @ 65 .025 @ 50 .025 @ 35	10	3.0	*750 nsec.	W
DI 914-1QM -2QM -3QM	3.5	75 60 45	.010 @ 65 .010 @ 50 .020 @ 35	20	3.0	*750 nsec.	W

DIODE QUAD BRIDGES

Part Number	$V_{BR}$ (Each Diode) Volts Min. @ $I_R = 100 \mu A$	$I_R$ (Each Diode) $\mu A$ Max. @ $V_R$ Volts	$I_F$ (Each Diode) mA Min. @ $V_F = 1.0V$	$C_T$ (Each Diode) pf Max.	$t_{rr}$ Max. (Each Diode) @ $I_F = 10mA$ ; recover to $I_R = -1 mA$	GEOM-ETRY
DI 914-1B -2B -3B	75 60 45	.010 @ 65 .010 @ 50 .010 @ 35	20	3.0	*750 nsec.	X

\*Also available with  $t_{rr}$  Max. @ 10 nsec.

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